



DH253 Hall-effect sensor is a temperature stable, stress-resistant switch. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

DH253 includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, open-drain output. Advanced CMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries.

DH253 is rated for operation between the ambient temperatures -40°C and $+85^{\circ}\text{C}$ for the E temperature range. The four package styles available provide magnetically optimized solutions for most applications. Package types SO is an SOT-23 (1.1 mm nominal height), SQ is an QFN2020-3 (0.55 mm nominal height), a miniature low-profile surface-mount package, while package UA is a three-lead ultra mini SIP for through-hole mounting.

The package type is in a Halogen Free version was verified by third party Lab.

Features and Benefits

- CMOS Hall IC Technology
- Solid-State Reliability much better than reed switch
- Omni polar output switches with absolute value of North or South pole from magnet
- Low power consumption (2.6mA)
- High Sensitivity for reed switch replacement
- 100% tested at 125°C for K.
- Small Size
- ESD HBM $\pm 4\text{KV}$ Min
- COST competitive

Applications

- Solid state switch
- Lid close sensor for power supply devices
- Magnet proximity sensor for reed switch replacement in high duty cycle applications.
- Safety Key on sporting equipment
- Revolution counter
- Speed sensor
- Position Sensor
- Rotation Sensor
- Safety Key

Absolute Maximum Ratings At ($T_a=25^{\circ}\text{C}$)

Characteristics		Values	Unit
Supply voltage, (V_{DD})		7	V
Output Voltage, (V_{out})		6	V
Reverse voltage, (V_{DD}) (V_{out})		-0.3	V
Magnetic flux density		Unlimited	Gauss
Output current, (I_{out})		25	mA
Operating Temperature Range, (T_a)	“E” version	-40 to +85	$^{\circ}\text{C}$
	“K” version	-40 to +125	$^{\circ}\text{C}$
Storage temperature range, (T_s)		-55 to +150	$^{\circ}\text{C}$
Maximum Junction Temp, (T_j)		150	$^{\circ}\text{C}$
Thermal Resistance	(θ_{JA}) UA / SO / SQ	206 / 543 / 543	$^{\circ}\text{C}/\text{W}$
	(θ_{JC}) UA / SO / SQ	148 / 410 / 410	$^{\circ}\text{C}/\text{W}$
Package Power Dissipation, (P_D) UA / SO / SQ		606 / 230 / 230	mW

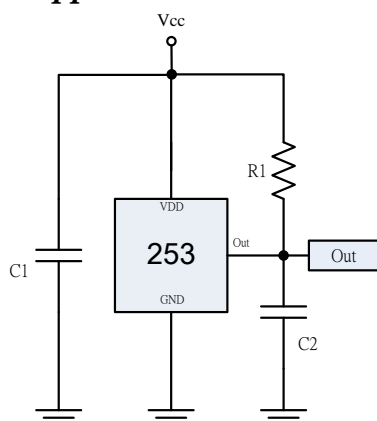
Note: Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability.

Electrical Specifications

DC Operating Parameters $T_A=+25^{\circ}\text{C}$, $V_{DD}=5.0\text{V}$

Parameters	Test Conditions	Min	Typ	Max	Units
Supply Voltage, (V_{DD})	Operating	2.5		6	V
Supply Current, (I_{DD})	Average		2.6	6.0	mA
Output Low Voltage, (V_{DSOL})	$I_{OUT}=10\text{mA}$			400	mV
Output Leakage Current, (I_{off})	I_{OFF} B<BRP, $V_{OUT} = 5\text{V}$			10	μA
Output Rise Time, (T_R)	$R_L=10\text{k}\Omega$, $C_L=20\text{pF}$			0.45	μs
Output Fall Time, (T_F)	$R_L=10\text{k}\Omega$; $C_L=20\text{pF}$			0.45	μs
Electro-Static Discharge	HBM	4			KV
Operate Point, (B_{OPS})	S pole to branded side, B > BOP, Vout On		30	60	Gauss
	N pole to branded side, B > BOP, Vout On	-60	-30		
Release Point (B_{RPS})	S pole to branded side, B < BRP, Vout Off	5	25		Gauss
	N pole to branded side, B < BRP, Vout Off		-25	-5	
Hysteresis, (B_{HYS})	$ B_{OPx} - B_{RPx} $		5		Gauss

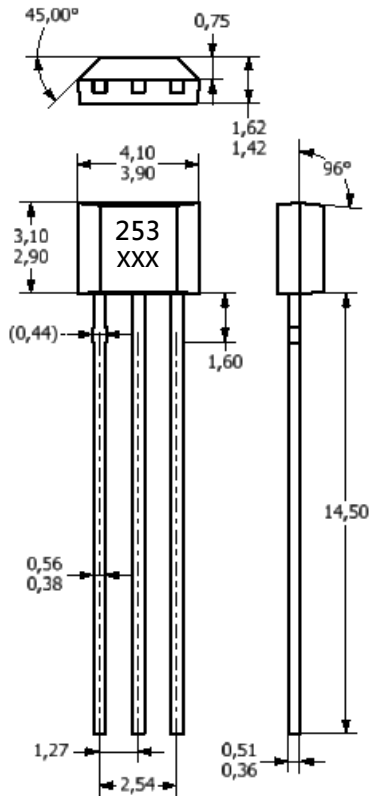
Typical Application circuit



C1 : 10nF
C2 : 100pF
R1 : 10K Ω

Sensor Location, Package Dimension and Marking MH253 Package

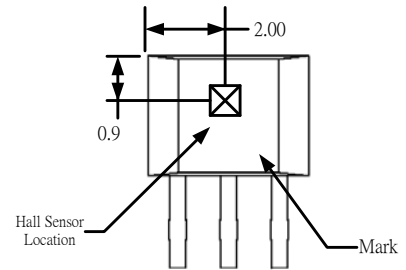
UA Package



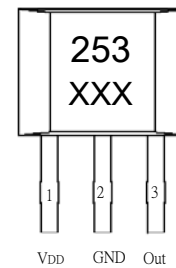
NOTES:

- 1).Controlling dimension: mm
- 2).Leads must be free of flash and plating voids
- 3).Do not bend leads within 1 mm of lead to package interface.
- 4).PINOUT:
Pin 1 VDD
Pin 2 GND
Pin 3 Output

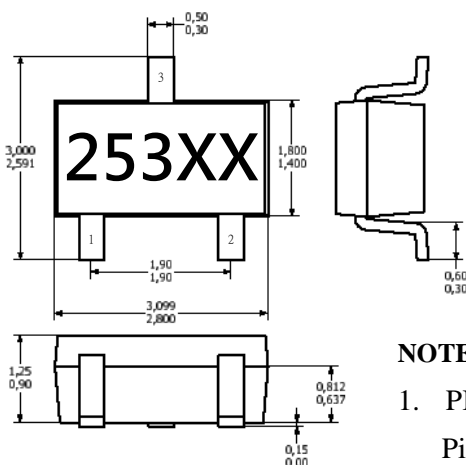
Hall Chip location



Output Pin Assignment (Top view)



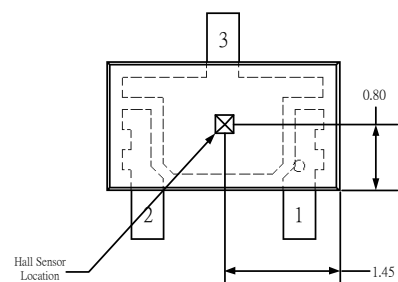
SO Package (Top View)



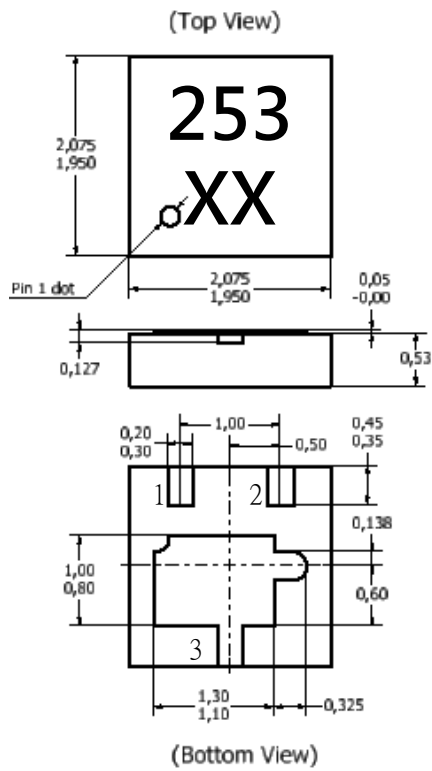
NOTES:

1. PINOUT (See Top View at left :)
Pin 1 V_{DD}
Pin 2 Output
Pin 3 GND
2. Controlling dimension: mm
3. Lead thickness after solder plating will be 0.254mm maximum

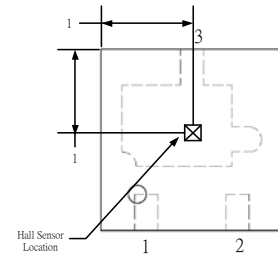
Hall Plate Chip Location (Bottom view)



SQ Package



**Hall Plate Chip Location
(Top view)**



NOTES:

1. PINOUT (See Top View at left)
 Pin 1 VDD
 Pin 2 Output
 Pin 3 GND
2. Controlling dimension: mm;
3. Chip rubbing will be 10mil maximum;
4. Chip must be in PKG. center.